

Improved Bipolar Junction Transistor

ABSTRACT OF THE INVENTION

An improved BJT is described that maximizes both BV_{CEO} and F_t/F_{max} for optimum performance. Scattering centers are introduced in the collector region (80) of the BJT to improve BV_{CEO} . The inclusion of the scattering centers allows the width of the collector region W_{CD} (90) to be reduced leading to an improvement in F_t/F_{max} .